

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 6,916,699 B1
DATED : July 12, 2005
INVENTOR(S) : Vishnu K. Agarwal

Page 1 of 2

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Title page.

Item [56], **References Cited**, U.S. PATENT DOCUMENTS,
"5,552,341 A 9/1996 Lee 438/668" should read
-- 5,552,341 A 9/1996 Lee 437/192 --.

Column 1.

Line 53, "tungsten nitride WN_x , wherein X is a number greater than" should read
-- tungsten nitride WN_x , wherein X is a number greater than --.

Column 2.

Line 4, "cause the oxygen at the tungsten nitride surface to diff-use" should read
-- cause the oxygen at the tungsten nitride surface to diffuse --.
Line 10, "coupled in series, wherein the HSG/ $Ta_2O_5WN_x$ layers serve" should read
-- coupled in series, wherein the HSG/ Ta_2O_5/WN_x layers serve --.
Line 14, " $Ta_2O_5WN_x$ /polysilicon capacitor that was intended to be" should read
-- Ta_2O_5/WN_x /polysilicon capacitor that was intended to be --.
Line 18, "as the bottom plate of a capacitor, underlying the Ta_2O_5 ," should read
-- as the bottom plate of a capacitor, underlying the Ta_2O_5 --.

Column 4.

Line 40, "nitride layer **28** exposed in situ to a N_2 and H_2 plasma The" should read
-- nitride layer **28** exposed in situ to a N_2 and H_2 plasma. The --.
Line 52, "(RF) power ranging from about 50 to about 1000 W; a" should read
-- (RF) power ranging from about 50 to about 1000W; a --.

Column 5.

Line 42, "ranging from about 50 to about 1000 W; a pressure ranging" should read
-- ranging from about 50 to about 1000W; a pressure ranging --.

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 6,916,699 B1
DATED : July 12, 2005
INVENTOR(S) : Vishnu K. Agarwal

Page 2 of 2

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Column 6.

Line 21, "used to provide the tungsten nitride layer **28** and one of the" should read
-- used to provide the tungsten nitride layer **28** and one of the --.

Signed and Sealed this

Twenty-first Day of March, 2006



JON W. DUDAS
Director of the United States Patent and Trademark Office